

Thyristor Module

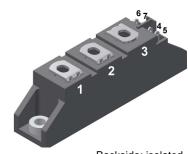
MCMA50P1200TA

V_{RRM}	<i>=</i> 2x 1200 V				
I _{tav}	=	50 A			
Vτ	=	1.17 V			

Phase leg

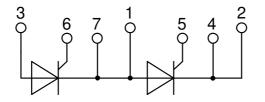
Part number

MCMA50P1200TA



Backside: isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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MCMA50P1200TA

Thyristo				1	Ratings		!
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{vJ} = 25^{\circ}C$			1300	· ·
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{vJ} = 25^{\circ}C$			1200	١
R/D	reverse current, drain current	V _{R/D} = 1200 V	$T_{vJ} = 25^{\circ}C$			100	μ
		V _{R/D} = 1200 V	$T_{vJ} = 140^{\circ}C$			6	m/
VT	forward voltage drop	$I_{T} = 50 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1.25	١
		$I_{T} = 100 \text{ A}$				1.48	١
		$I_{T} = 50 \text{ A}$	T _{vJ} = 125°C			1.17	١
		$I_{T} = 100 \text{ A}$				1.44	١
I _{tav}	average forward current	T _c = 85°C	T _{vJ} = 140°C			50	1
T(RMS)	RMS forward current	180° sine				79	/
ν _{το}	threshold voltage		T _{v.i} = 140°C			0.89	١
r _τ	slope resistance } for power lo	oss calculation only	vo			5.3	m
R _{thJC}	thermal resistance junction to cas	e .				0.7	
R _{thCH}	thermal resistance case to heatsi				0.2	•••	K/V
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$		0.2	160	٧
_	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v_i} = 45^{\circ}C$			800	
TSM	max. Iorward burge burrent	t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			865	
		t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$\frac{v_{R}}{T_{V,I}} = 140^{\circ}C$			680	,
	under for funcion	t = 8,3 ms; (60 Hz), sine	$\frac{V_{R} = 0 V}{T_{R} + 1500}$			735	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			3.20	
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			3.12	
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 140 ^{\circ}\text{C}$			2.31	kA ²
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			2.25	kA ²
C	junction capacitance	$V_{R} = 400 V$ f = 1 MHz	$T_{vJ} = 25^{\circ}C$		32		pl
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 140^{\circ}C$			10	۷
		t _P = 300 μs				5	۷
P _{GAV}	average gate power dissipation					0.5	۷
(di/dt) _{cr}	critical rate of rise of current	T _{vJ} = 140 °C; f = 50 Hz re	epetitive, $I_{T} = 150 \text{ A}$			150	A/μ
		t_{P} = 200 µs; di _G /dt = 0.45 A/µs; -					
		$I_{G} = 0.45 \text{ A}; \text{ V} = \frac{2}{3} \text{ V}_{DRM}$ no	on-repet., $I_{\tau} = 50 \text{ A}$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{\text{DBM}}$	T _{vJ} = 140°C			1000	V/µ
		R _{GK} = ∞; method 1 (linear volta	ge rise)				
V _{gt}	gate trigger voltage	$V_{\rm D} = 6 \text{ V}$	$T_{vJ} = 25^{\circ}C$			1.5	١
- 01			$T_{yJ} = -40 ^{\circ}\text{C}$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			78	m/
GI	gale ligger ear ent		$T_{vj} = -40^{\circ}C$			200	
V _{gd}	gate non-trigger voltage	$V_{D} = \frac{2}{3} V_{DBM}$	$T_{VJ} = 40^{\circ} \text{C}$ $T_{VJ} = 140^{\circ} \text{C}$			0.2	۱
	gate non-trigger current	$\mathbf{v}_{\mathrm{D}} = 73 \mathbf{v}_{\mathrm{DRM}}$	1 _{VJ} = 140 O			5	i .
		10	т огос				m/
I.	latching current	$t_p = 10 \ \mu s$	$T_{vJ} = 25 \degree C$			200	m/
_		$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$					
I _H	holding current	$V_{\rm D} = 6 \ V \ R_{\rm GK} = \infty$	$T_{VJ} = 25 \degree C$			100	1
t _{gd}	gate controlled delay time	$V_{D} = \frac{1}{2} V_{DRM}$	$T_{vJ} = 25 ^{\circ}C$			2	μ
		$I_{\rm G} = 0.45 \text{A}; di_{\rm G}/dt = 0.45 \text{A}/\mu \text{s}$					
t _q	turn-off time	$V_{R} = 100 \text{ V}; I_{T} = 50\text{ A}; \text{ V} = 2$	⅓ V _{DRM} T _{VJ} =125 °C		150		μ
		$di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 20 \text{ V}.$	/μs t _p = 200 μs				:

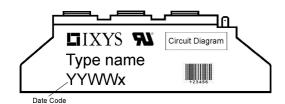
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20191209d



MCMA50P1200TA

Package TO-240AA				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					100	Α
T _{vj}	virtual junction temperature				-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque		2.5		4	Nm		
d _{Spp/App}	creepage distance on surface striking distance through		terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}			terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			4800			۷
	t = 1 minute		50/60 Hz, RMS; lıso∟ ≤ 1 mA		4000			V



Part description

M = Module C = Thyristor (SCR) M = Thyristor A = (up to 1800V) 50 = Current Rating [A] P = Phase leg 1200 = Reverse Voltage [V] TA = TO-240A-1B

TA = TO-240AA-1B

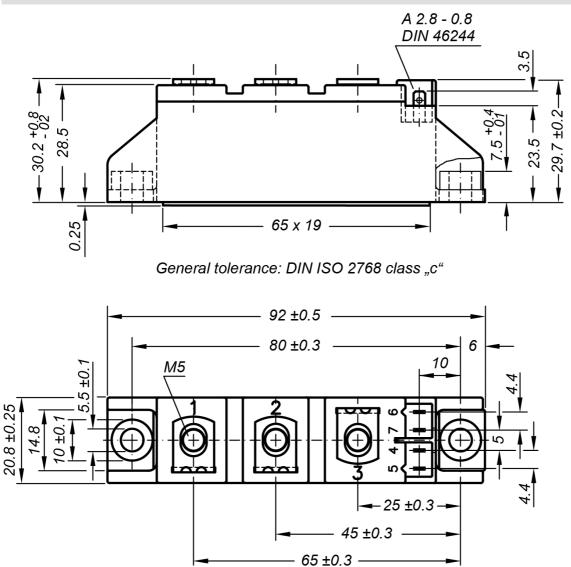
[Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MCMA50P1200TA	MCMA50P1200TA	Box	36	513943

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140^{\circ}C$
)[Thyristor		
V _{0 max}	threshold voltage	0.89		V
$\mathbf{R}_{0 \max}$	slope resistance *	4.1		mΩ

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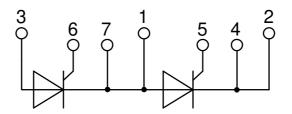


Outlines TO-240AA



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 200L (L = Left for pin pair 4/5) Type ZY 200R (R = Right for pin pair 6/7) UL 758, style 3751



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MCMA50P1200TA



Thyristor

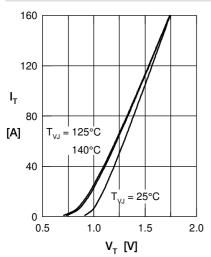


Fig. 1 Forward characteristics

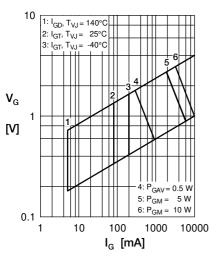


Fig. 4 Gate voltage & gate current

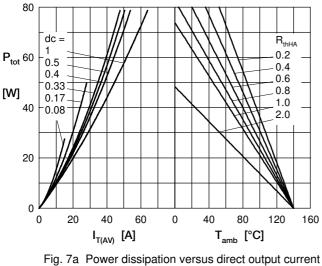
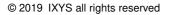
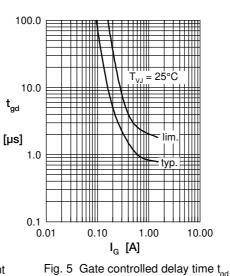


Fig. 7b and ambient temperature







50 Hz, 80% V

 T_{VJ}

0.1

t [s]

 \mathbf{I}_{TSM} : crest value, t: duration

0.80

Fig. 2 Surge overload current

45°C

800

ITSM

[A]

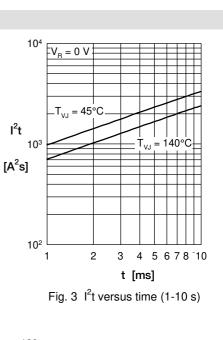
400

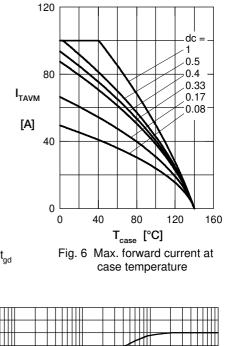
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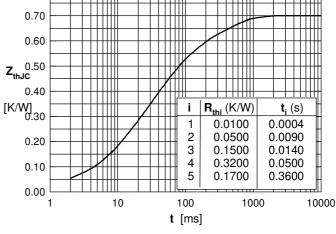
0.01

νı

140°C









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